

Poster Presentation

[AMDp1]Oxide TFTs

Thu. Nov 28, 2019 10:40 AM - 1:10 PM Main Hall (1F)

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[AMDp1-21L]Improved Mobility and Stability of Indium-free Oxide Thin Film Transistor by Metal Capping Layer

*Ji-Min Park¹, Ho-Hyun Nahm², Hyun-Suk Kim¹ (1. Chungnam National University (Korea), 2. Korea Advanced Institute of Science and Technology (Korea))

Keywords:thin film transistors, amorphous oxide semiconductors, BaSnO₃, high mobility, stability

In this work, to get better electrical properties, metal capping layer and lift-off lithography process of a new type of Indium-free amorphous thin films and associated thin-film transistors (TFTs) were investigated. As a result, optimized TFTs showed high mobility ($>30\text{cm}^2/\text{Vs}$) and excellent stability than conventional InZnO TFTs.